

Features

- -30V/-3.9A,
 $R_{DS(ON)} = 52m\Omega(Typ.)@V_{GS} = -10V$
 $R_{DS(ON)} = 60m\Omega(Typ.)@V_{GS} = -4.5V$
 $R_{DS(ON)} = 78m\Omega(Typ.)@V_{GS} = -2.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged

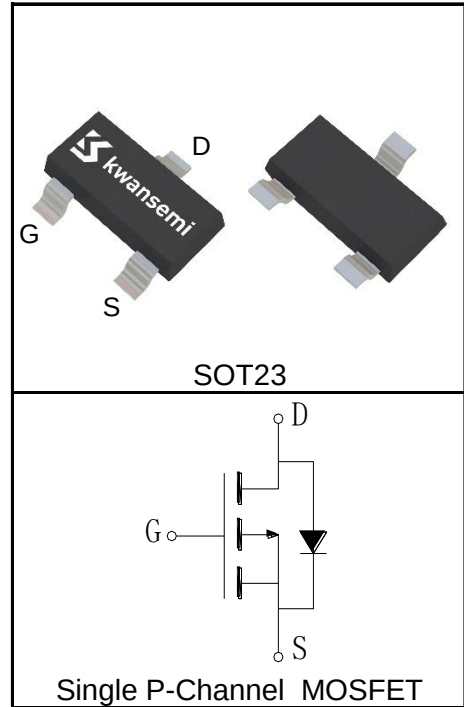
Applications

- Load Switch



Halogen-Free

Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±12	
T _{Jmax}	Maximum Junction Temperature		150	°C
T _J ,T _{STG}	Operating and Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _A =25°C	-1.2	A
Mounted on Large Heat Sink				
I _{DP} ^①	300μs Pulse Drain Current Tested	T _A =25°C	-15	A
I _D ^②	Continuous Drain Current(V _{GS} =-10V)	T _A =25°C	-3.9	A
		T _A =70°C	-3.1	
P _D	Maximum Power Dissipation	T _A =25°C	1	W
		T _A =70°C	0.64	
R _{θJL}	Thermal Resistance-Junction to Lead		80	°C/W
R _{θJA} ^③	Thermal Resistance-Junction to Ambient		125	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^④	Avalanche Energy, Single Pulsed		20	mJ

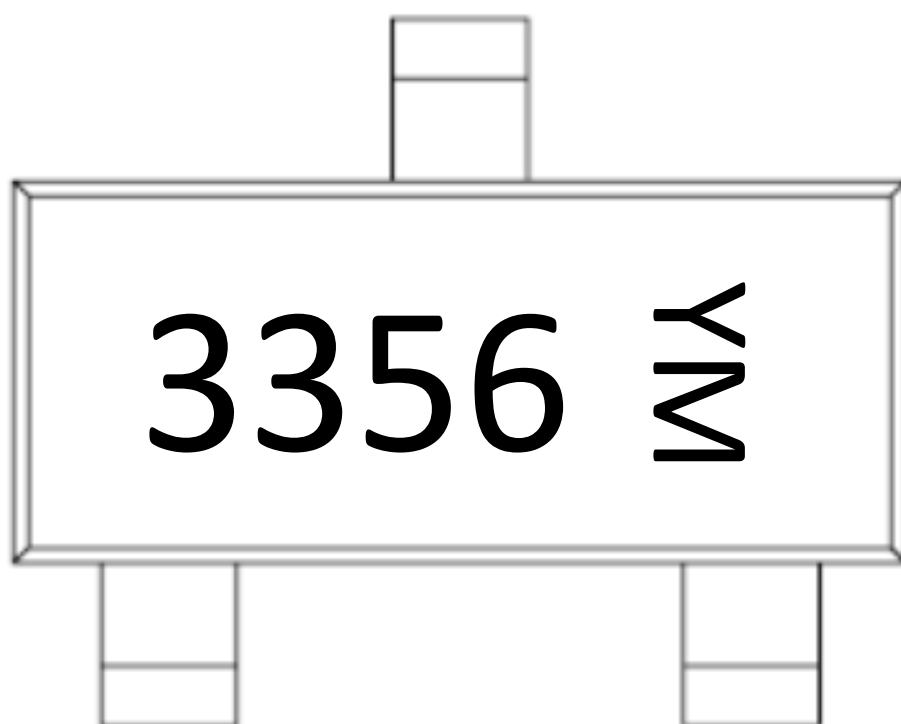
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS3356AA			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V			-1	μA
			T _J =125°C			
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-0.5	-0.9	-1.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±12V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-3A		52	65	mΩ
		V _{GS} =-4.5V, I _{DS} =-2A		60	80	mΩ
		V _{GS} =-2.5V, I _{DS} =-1A		78	120	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =-3A, V _{GS} =0V		-0.85	-1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =-3A, dI _{SD} /dt=-100A/μs		12		ns
Q _{rr}	Reverse Recovery Charge			7		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		11		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz		690		pF
C _{oss}	Output Capacitance			45		
C _{rss}	Reverse Transfer Capacitance			40		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, I _{DS} =-3A, V _{GEN} =-10V, R _G =6Ω		5		ns
t _r	Turn-on Rise Time			7		
t _{d(OFF)}	Turn-off Delay Time			26		
t _f	Turn-off Fall Time			9		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-10V, I _{DS} =-3A		8.5		nC
Q _{gs}	Gate-Source Charge			1.9		
Q _{gd}	Gate-Drain Charge			2.6		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , Starting $T_J = 25^{\circ}\text{C}$, $I_{ASmax} = -9A$, $L = 0.5\text{mH}$, $V_{DD} = -15V$, $R_G = 25\Omega$, $V_{GS} = -10V$. Part not recommended for use above this value.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

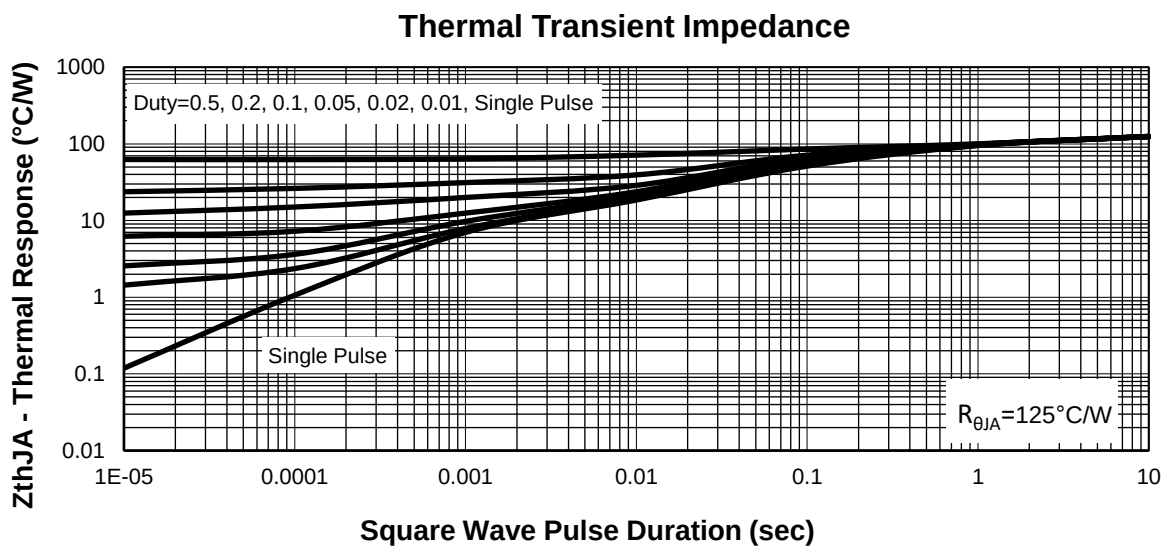
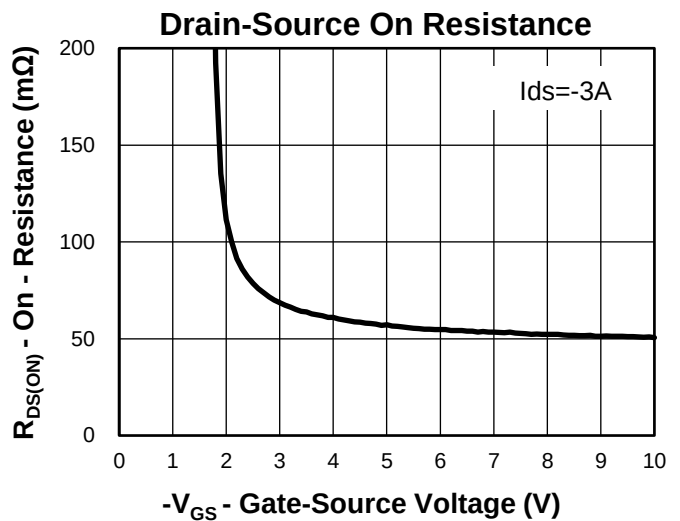
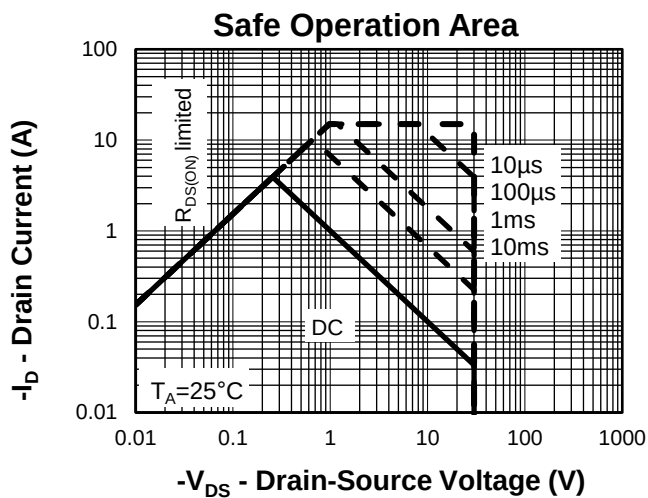
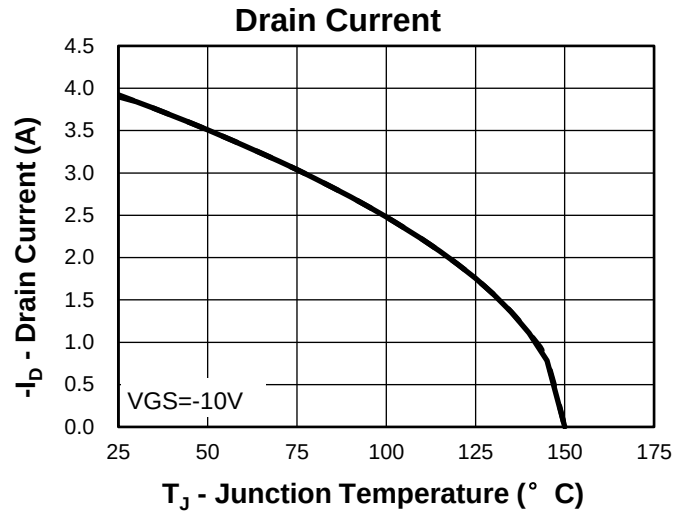
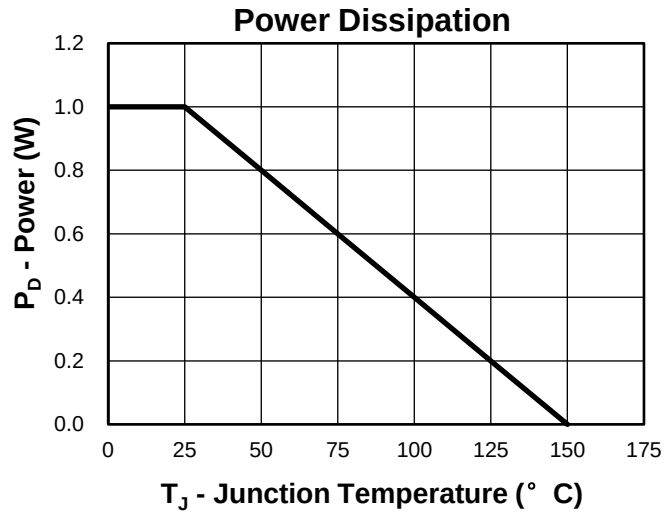
Device	Package	Packaging	Quantity	Reel Size	Tape width
KS3356AA	SOT23	Tape&Reel	3000	7"	8mm



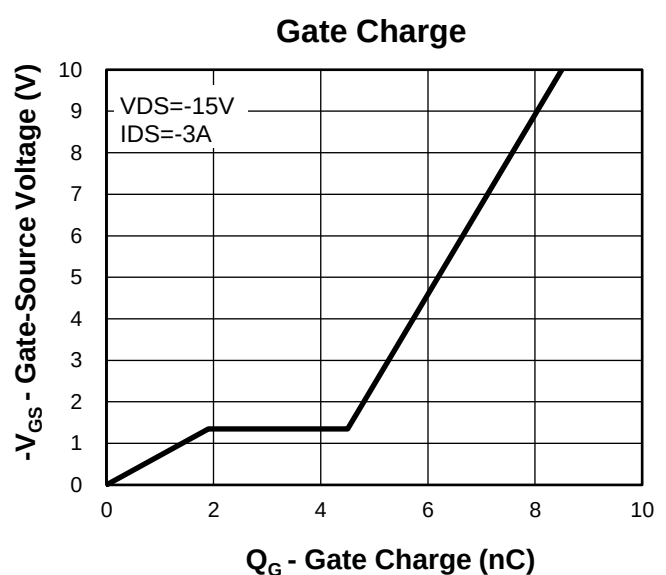
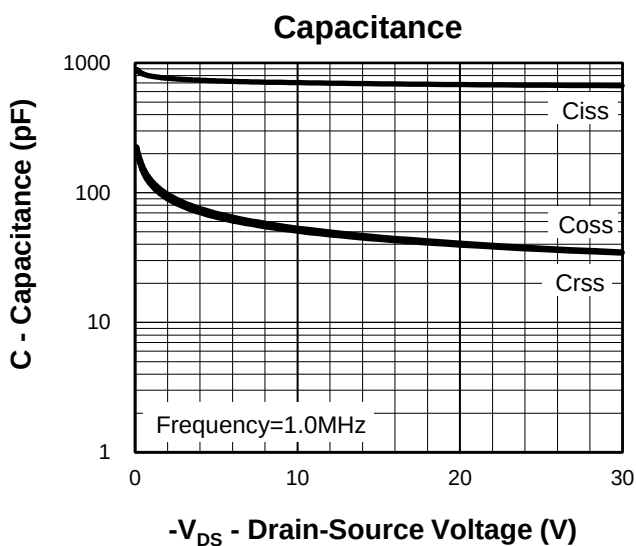
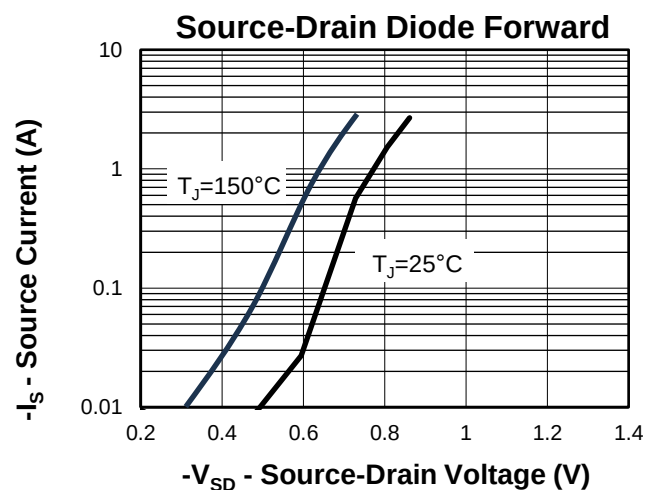
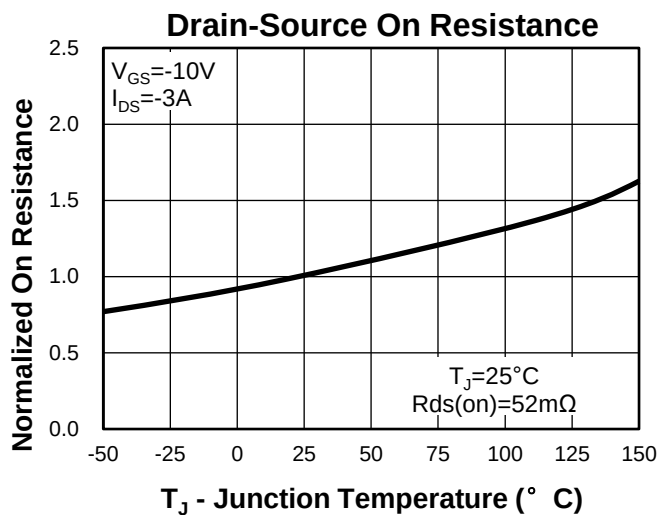
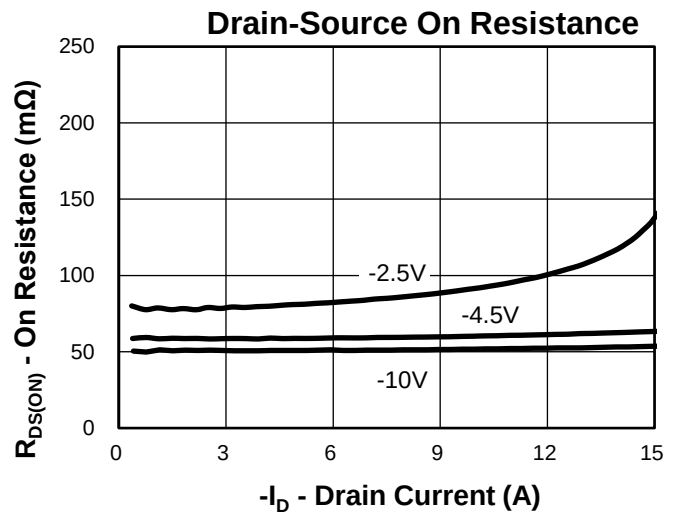
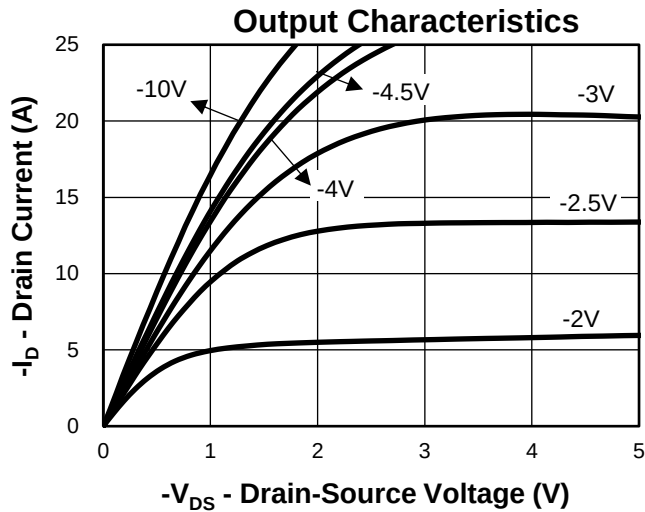
Y =Year,2017-A,2018-B,etc.

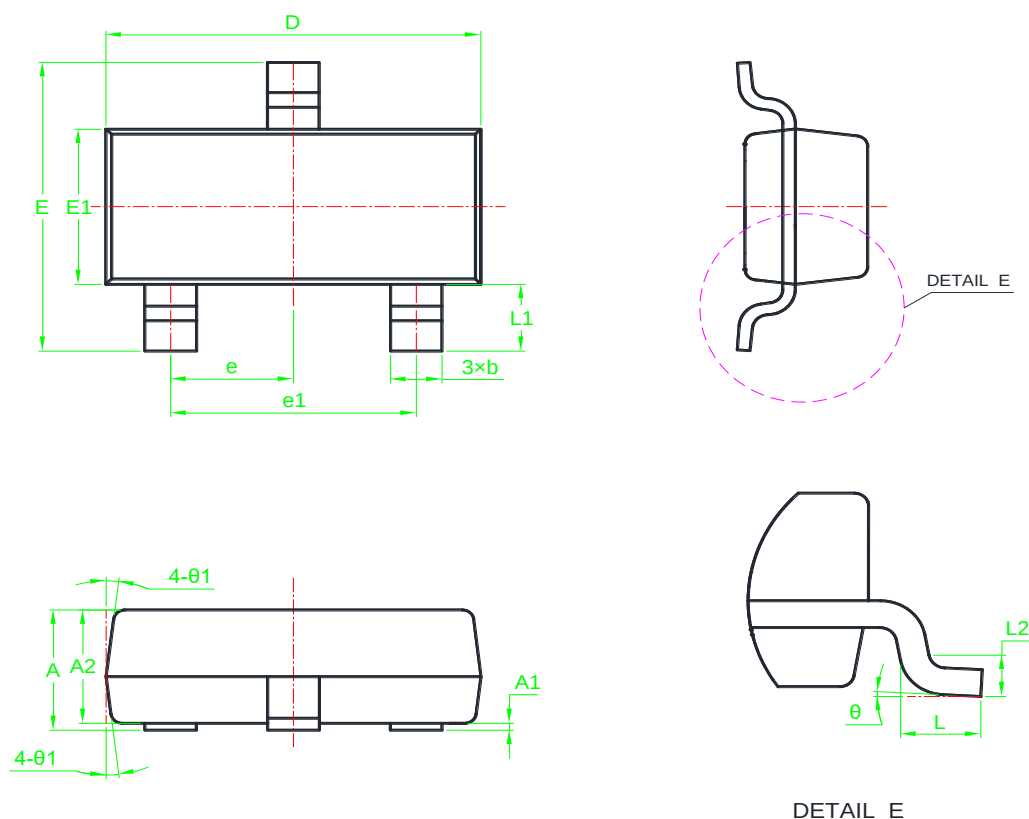
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Typical Characteristics



Typical Characteristics

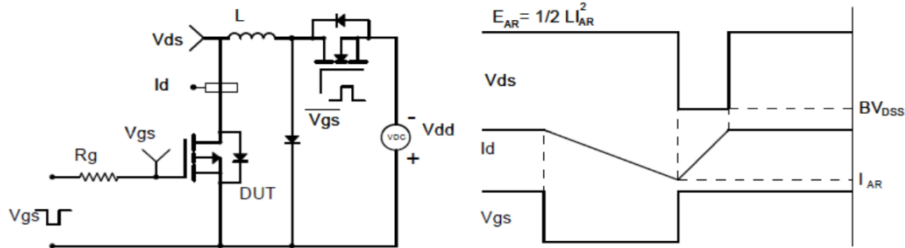


Package Information
SOT23


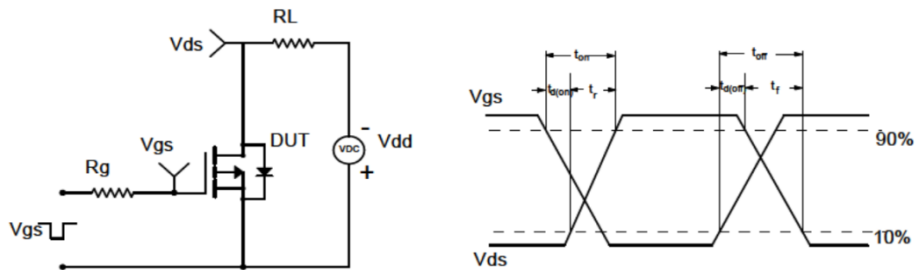
SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	*	1.12	0.035	*	0.044	e	0.95BSC			0.037BSC		
A1	0.01	*	0.10	0.000	*	0.004	e1	1.90BSC			0.075BSC		
A2	0.80	0.90	1.02	0.031	0.035	0.040	L	0.30	0.40	0.50	0.012	0.016	0.020
b	0.30	0.40	0.50	0.012	0.016	0.020	L1	0.54REF			0.021REF		
D	2.80	2.90	3.00	0.110	0.114	0.118	L2	0.254BSC			0.010BSC		
E	2.25	2.40	2.55	0.089	0.094	0.100	θ	0°	*	8°	0°	*	8°
E1	1.20	1.30	1.40	0.047	0.051	0.055	θ 1	0°	*	10°	0°	*	10°

Note: Dimensions do not inclusive burrs and mold flash.

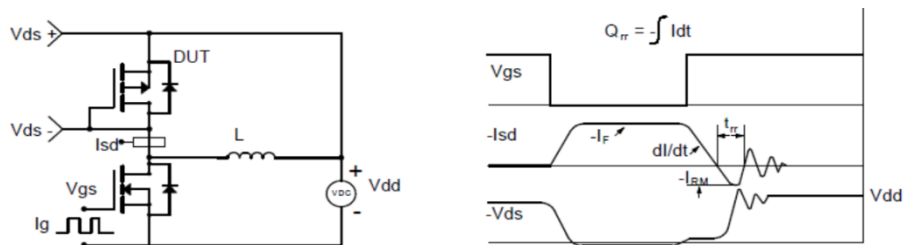
Avalanche Test Circuit and Waveforms



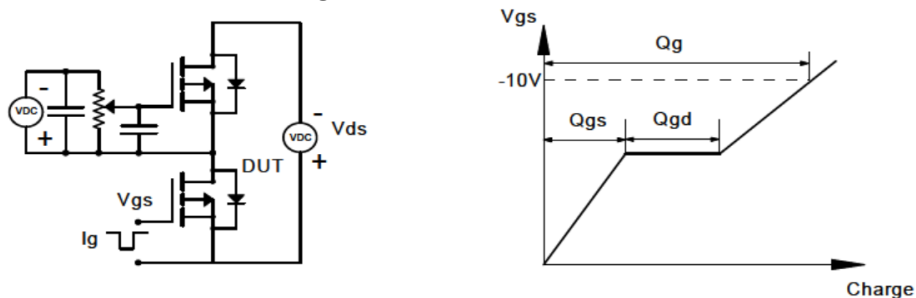
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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